

- AMR sensor
- Very high sensitivity
- Almost no hysteresis
- **Various applications**
- **Available with internal magnet**
- Available in several packages

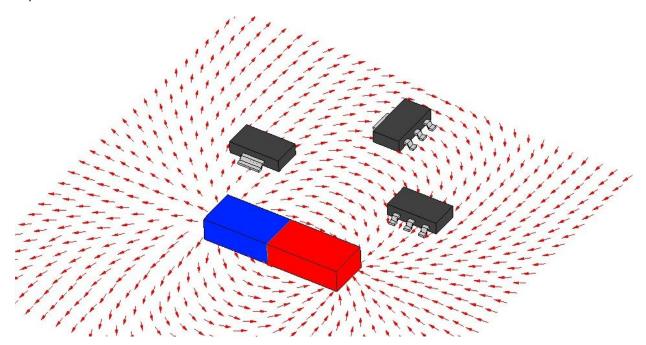
KMY22

KMY20

KMZ20

DESCRIPTION

Due to its featured properties - high sensitivity and almost no hysteresis - the KMY / KMZ sensors are used in a wide range of applications, like magnetic field measurement, revolution counters, proximity detecting, and position measurement.



An uniaxial linear magnetic field will generate a linear output within the specified magnetic field range.

FEATURES

- Output proportional to magnetic field strength with very high sensitivity
- Very small hysteresis
- Large operating temperature range, from -40°C up to +150 °C
- Highly reliable
- With / without internal magnet

APPLICATIONS

- Detection of very weak magnetic fields, like earth magnetic field, or field generated by small magnetic particles
- Detection of objects that distort non-local magnetic fields
- Revolution measurement on ferromagnetic gears
- **Contactless switch**
- Contactless displacement / position sensor

DESCRIPTION

An uniaxial linear magnetic field (in y-direction) will generate a linear output within the specified magnetic field range. The sensor is available in two types: the KMY 20 M, KMY 21 M and KMZ 20 M sensor types contain intrinsic magnets which provide an auxiliary magnetic field (in x-direction) at the sensor die which prevents magnetic domains from flipping irregularly.

Auxiliary Field Dependence

If the dies MR174B or the components KMY22, KMY20S or KMZ20S are used, the auxiliary field has to be provided by the user. The dependence of the sensitivity with auxiliary field strength is depicted in the figure aside.

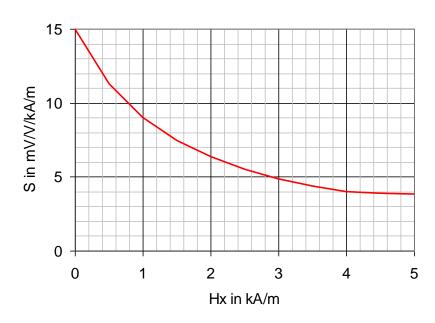


Figure 1: Sensitivity dependence on auxiliary field strength

Auxiliary field strengths below Hx<1.5 kA/m are not recommended, as small disturbances may flip the magnetization domains. Sometimes, the magnetic conditions in the application may provide enough Hx bias field stabilization. MEAS Germany can provide advise for customer specific magnet arrangements.

If a bias field Hx is not applied or Hx is less than 2.5 kA/m, the sensor may be used only in a limited field range Hy, depending on the present total bias field Hx,tot. In this case, it is strongly recommended to 'premagnetize' the sensor, i.e. align all magnetic domains consistently, prior to the measurement.

Hx,tot is the sum of all acting magnetic fields in x direction at the sensor die.

Do not use the sensor outside the safe operating area. Leaving the save operating area can destroy an existing premagnetization and therefore will lead to unreproducible sensor signals.



Figure 2: Safe operating area

CHARACTERISTIC VALUES / SENSOR SPECIFICATIONS

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Operating Limits	-						
max. supply voltage	$V_{cc,max}$				10	V	
max. current	I _{cc,max}				9	mA	
operating temperature	T _{op}		-40		+150	°C	
storage temperature	T _{st}		-40		+150	°C	
General Sensor Specific	cations						
TC of amplitude	TCSV	Condition A, C	-0.36	-0.32	-0.28	%/K	
TC of resistance	TCBR	Condition A, C	+0.27	+0.32	+0.37	%/K	
TC of offset	TCVoff	Condition A, C	-4	0	+4	μV/V/K	
Sensor Specifications P	(MY 20 S, KN	MZ 20 S (T=25 °C, Hx=3 kA	/m external	lly)			
Supply voltage	V _{cc}	Condition A, B		5		V	
Bridge resistance	R _b	Condition A, B	1200	1700	2200	Ω	
Output signal range	$\Delta V_0/V_{cc}$	Condition A, B	16	20	24	mV/V	
Offset voltage	V _{off} /V _{cc}	Condition A, B	-1	0	+1	mV/V	
Sensitivity	S	Condition A, B	3.7	4.7	5.7	mV/V/kA/m	
Hysteresis	V _H /V _{cc}	Condition A, B	-	-	50	μV/V	
Sensor Specifications P	(MY 20 M, KI	MZ 20 M (T=25 °C, Hx=1.5±	0.5 kA/m ir	nternally)			
Supply voltage	V_{cc}	Condition A, B		5		V	
Bridge resistance	R _b	Condition A, B	1200	1700	2200	Ω	
Output signal range	$\Delta V_0/V_{cc}$	Condition A, B	16	20	24	mV/V	
Offset voltage	V _{off} /V _{cc}	Condition A, B	-1.5	0	+1.5	mV/V	
Sensitivity	S	Condition A, B	4	5.5	7	mV/V/kA/m	
Hysteresis	V _H /V _{cc}	Condition A, B	-	-	50	μV/V	
Sensor Specifications P	(MY 21 M (T=	25 °C, Hx=2.5±1.0 kA/m ir	nternally)				
Supply voltage	V _{cc}	Condition A, B		5		V	
Bridge resistance	R _b	Condition A, B	1100	1500	1900	Ω	
Output signal range	$\Delta V_0/V_{cc}$	Condition A, B	8	9.5	12	mV/V	
Offset voltage	V _{off} /V _{cc}	Condition A, B	48	50	52	%Vcc	
Sensitivity	S	Condition A, B	2.05	2.50	3.10	mV/V/kA/m	
Hysteresis	V _H /V _{cc}	Condition A, B	-	-	50	μV/V	

Stress above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.

MEASUREMENT CONDITIONS

Parameter	Symbol	Unit	Condition		
Condition A: Set Up Co	onditions				
Ambient temperature	Т	°C	23±5 Measurement results are extrapolated to 25°C by using the given temperature coefficients		
Supply voltage	V _{cc}	V	5		
Output voltage	V ₀ V ₀ /V _{cc}	mV mV/V	$\begin{array}{c} V_{0} = (V_{0+} - V_{0-}) \\ \text{Output voltages are also given independently on supply} \\ \text{voltage: example: Vo/Vcc} = (V_{0+} - V_{0-})/Vcc; \\ \text{measure MR half bridge against reference half bridge} \end{array}$		
Reference half bridge			2* 2 kΩ 0.1% (KMY21M only)		
for full bridge sensors (KMY20S, KMY20M, KMY22, KMZ20S, KMZ20M)			for half bridge sensors (KMY 21 M)		
VCC KMY20X 3 V0 2 2 V0-			The output voltage of the MR half bridge is measured against a reference half bridge		
Condition B: Sensor S	pecifications	(T=25 °C, S-Type:	Hx=3.0±0.5 kA/m)		
Output voltage range	$\Delta V_{O}/V_{cc}$	mV/V	$H_y = -7+7 \ kA/m; \ \Delta V_O = (V_{O,\text{max}} - V_{O,\text{min}})$		
Offset voltage	V _{off} /V _{cc}	mV/V	$H_y = 0; \ V_{off} = V_o(H_y)$		
Sensitivity	S	(mV/V)/(kA/m)	$H_{y} = 1kA/m; S := \frac{V_{0}(+H_{y}) - V_{0}(-H_{y})}{2 \cdot V_{cc}}$		
Hysteresis V_H/V_{cc} $\mu V/V$			Hy in kA/m $(V_0(H_y=0;H_y=-1 \rightarrow +1)$		
			$-V_0(H_y = 0; H_y = +1 \rightarrow -1))/V_{cc}$		

Ambient temperatures	T	°C	T ₁ =-25 °C, T ₀ =+25 °C, T ₂ =+125 °C
TC of amplitude	TCSV	%/K	$TCV = \frac{1}{(T_2 - T_1)} \cdot \frac{\Delta V_0 / V_{cc}(T_2) - \Delta V_0 / V_{cc}(T_1)}{\Delta V_0 / V_{cc}(T_1)} \cdot 100\%$
TC of resistance	TCBR	%/K	$TCR = \frac{1}{(T_2 - T_1)} \cdot \frac{R(T_2) - R(T_1)}{R(T_1)} \cdot 100\%$
TC of offset	TCVoff	(μV/V)/K	$TCVoff = \frac{Voff(T_2) - Voff(T_1)}{(T_2 - T_1)}$

SENSOR MODELS

KMY 20 / KMY 22 / KMZ 20

The KMY and KMZ sensors are highly sensitive magnetic field sensors which utilize the anisotropic magneto resistance effect. The KMY 20 and KMZ 20 sensors contain a Wheatstone bridge.

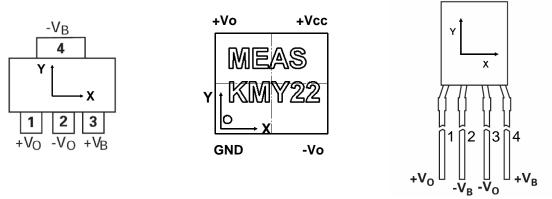


Figure 3: Pad annotation and definition of field direction for KMY & KMZ

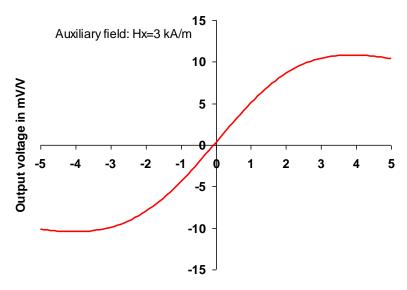
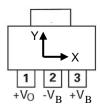


Figure 4: Characteristic output curve of KMY 20 S resp. KMZ 20 S for an auxiliary field strength of Hx=3 kA/m

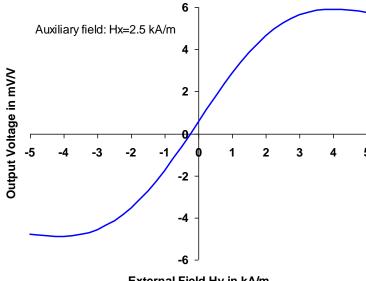
Field Strength Hy in kA/m

KMY 21

In contrast to the KMY20 sensor products, the KMY 21 M consists of a half bridge, making the sensor well suited for dynamic measurements.



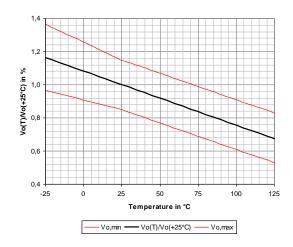
It contains an internal magnet, which provides an auxiliary filed of approx. 2.5 kA/m.



External Field Hy in kA/m

Figure 5: Characteristic curve for KMY21M

TEMPERATURE DEPENDENCIES



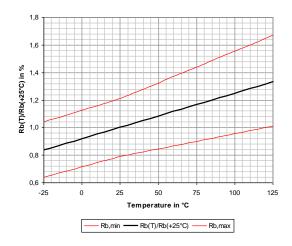
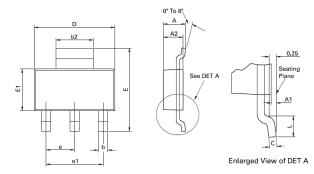


Figure 6: signal amplitude related to room temperature value

Figure 7: bridge resistance related to room temperature value

PACKAGES

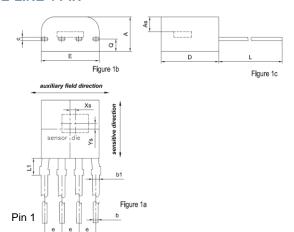
SOT223



Recommended solder reflow process for all packages according to IPC/JEDEC J-STD-020D (Pb-Free Process)

DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	-	1.80	-	0.071	е	2.30	BSC	0.090	5 BSC
A1	0.02	0.10	0.0008	0.004	e1	4.60	BSC	0.181	BSC
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

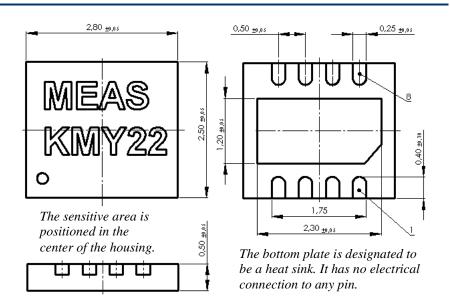
E-LINE 4 PIN



		Milimeter		Inches		
DIE POS.	KMZ20S	KMZ20M	tolerances	KMZ20S	KMZ20M	tolerances
Xs	+0.05	+0.05	+/-0.10	+0.002	+0.002	+/-0.004
Ys	+0.50	+0.50	+/-0.10	+0.02	+0.02	+/- 0.004
As	1.05	1.05	+/-0.10	0.041	0.041	+/-0.004

		Millmeter		Inches			
DIM	min.	typ.	max.	min.	typ.	max.	
Α	2.4		2.8	0.094		0.110	
b	0,35		0,48	0.0138		0,0189	
b1	0.45		0.60	0.0178		0.024	
С	0.25		0.35	0.0098		0.0138	
D	4.0		4.4	0.157		0.173	
Е	3.8		4.4	0.150		0.173	
L	12.0		14.0	0.472		0.551	
е	NOM. 1.25			NOM. 0.049			
L1	1.1		1.3	0.043		0.051	

UTDFN8 2.5X2.8 MM



DIE

Die layout and dimensions on request.

ORDERING CODE

DEVICE	DIE	PACKAGE	INTERNAL MAGNET	PART NUMBER
KMY 20 S	full bridge	SOT-223	NO	G-MRCO-006
KMY 20 M	full bridge	SOT-223	YES	G-MRCO-001
KMY 21 M	half bridge	SOT-223	YES	G-MRCO-011
KMZ 20 S	full bridge	E-Line	NO	G-MRCO-007
KMZ 20 M	full bridge	E-Line	YES	G-MRCO-003
KMY 22	full bridge	UTDFN8	NO	on request



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